

(43) International Publication Date
14 July 2011 (14.07.2011)(10) International Publication Number
WO 2011/084752 A2(51) International Patent Classification:
H01L 21/3105 (2006.01) *H01L 21/314* (2006.01)(21) International Application Number:
PCT/US2010/061356(22) International Filing Date:
20 December 2010 (20.12.2010)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
61/293,082 7 January 2010 (07.01.2010) US
12/972,711 20 December 2010 (20.12.2010) US(71) Applicant (for all designated States except US): **APPLIED MATERIALS, INC.** [US/US]; 3050 Bowers Avenue, Santa Clara, California 95054 (US).

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(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PE, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG,

[Continued on next page]

(54) Title: IN-SITU OZONE CURE FOR RADICAL-COMPONENT CVD

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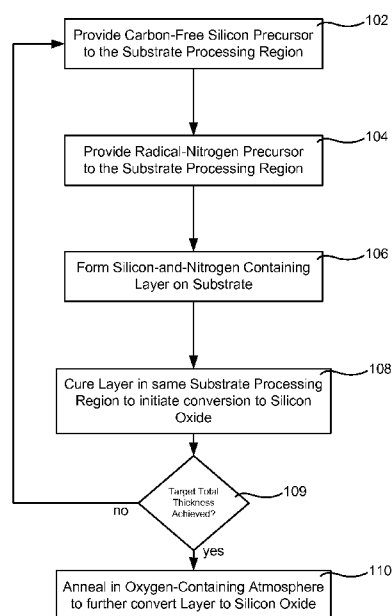


FIG 1

(57) Abstract: Methods of forming a dielectric layer are described. The methods include the steps of mixing a silicon-containing precursor with a plasma effluent, and depositing a silicon-and-nitrogen-containing layer on a substrate. The silicon-and-nitrogen-containing layer is converted to a silicon-and-oxygen-containing layer by curing in an ozone-containing atmosphere in the same substrate processing region used for depositing the silicon-and-nitrogen-containing layer. Another silicon-and-nitrogen-containing layer may be deposited on the silicon-and-oxygen-containing layer and the stack of layers may again be cured in ozone all without removing the substrate from the substrate processing region. After an integral multiple of dep-cure cycles, the conversion of the stack of silicon-and-oxygen-containing layers may be annealed at a higher temperature in an oxygen-containing environment.



ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

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